



WS3A008120E

Silicon Carbide Schottky Diode

V_{RRM}	=	1200	V
$I_F (T_C \leq 135^\circ\text{C})$	=	12	A
Q_C	=	23	nC

Features

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on V_F
- Temperature-independent Switching
- 175°C Operating Junction Temperature

Benefits

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

Package



Part Number	Package	Marking
WS3A008120E	TO-252	WS3A008120E

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{RRM}	Repetitive Peak Reverse Voltage	1200	V	$T_C = 25^\circ\text{C}$	
V_{RSM}	Surge Peak Reverse Voltage	1200	V	$T_C = 25^\circ\text{C}$	
V_R	DC Blocking Voltage	1200	V	$T_C = 25^\circ\text{C}$	
I_F	Forward Current	24.5 12 8	A	$T_C \leq 25^\circ\text{C}$ $T_C \leq 135^\circ\text{C}$ $T_C \leq 154^\circ\text{C}$	
I_{FSM}	Non-Repetitive Forward Surge Current	80	A	$T_C = 25^\circ\text{C}$, $t_p = 8.3\text{ms}$, Half Sine Wave	
P_{tot}	Power Dissipation	136	W	$T_C = 25^\circ\text{C}$	Fig.3
T_C	Maximum Case Temperature	154	$^\circ\text{C}$		
T_J, T_{STG}	Operating Junction and Storage Temperature	-55 to 175	$^\circ\text{C}$		
	TO-252 Mounting Torque	1	Nm	M3 Screw	

Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_F	Forward Voltage	1.55 2.2	1.8 2.5	V	$I_F = 8A, T_J = 25^\circ C$ $I_F = 8A, T_J = 175^\circ C$	Fig.1
I_R	Reverse Current	1 8	20 100	μA	$V_R = 1200V, T_J = 25^\circ C$ $V_R = 1200V, T_J = 175^\circ C$	Fig.2
C	Total Capacitance	520 38 30	/	pF	$V_R = 0V, T_J = 25^\circ C, f = 1MHz$ $V_R = 400V, T_J = 25^\circ C, f = 1MHz$ $V_R = 800V, T_J = 25^\circ C, f = 1MHz$	Fig.5
Q_C	Total Capacitive Charge	23	/	nC	$V_R = 800V, I_F = 8A$ $di/dt = 200A/\mu s, T_J = 25^\circ C$	Fig.4

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.1	$^\circ C/W$	Fig.6
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	80	$^\circ C/W$	
T_{sold}	Soldering Temperature	260	$^\circ C$	

Typical Performance

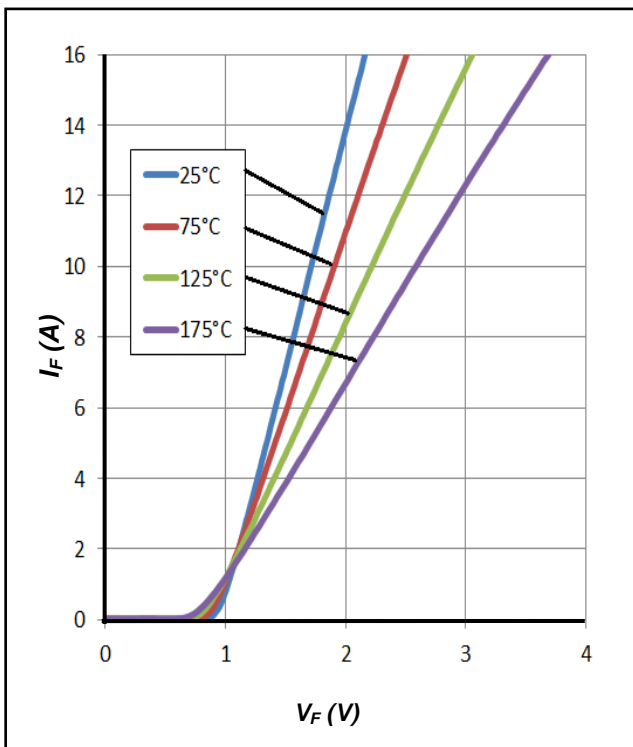


Figure 1. Forward Characteristics

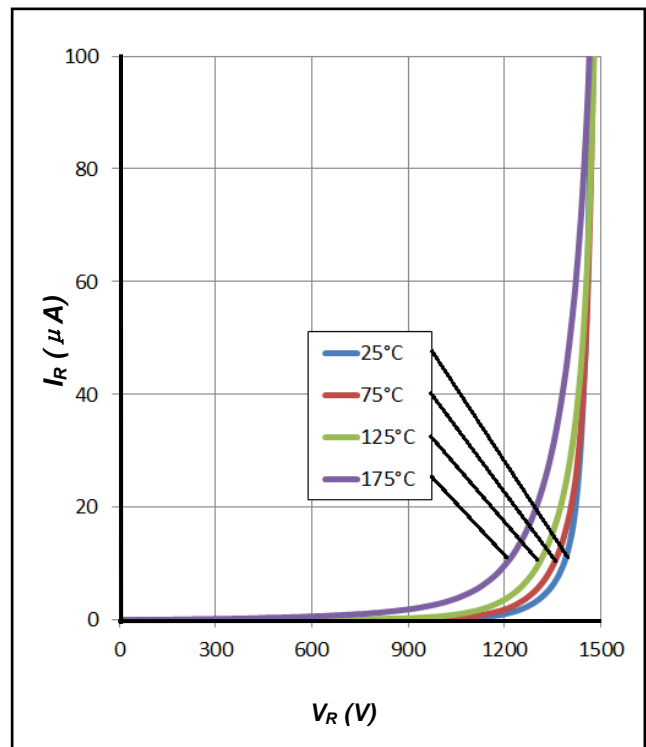


Figure 2. Reverse Characteristics

Typical Performance

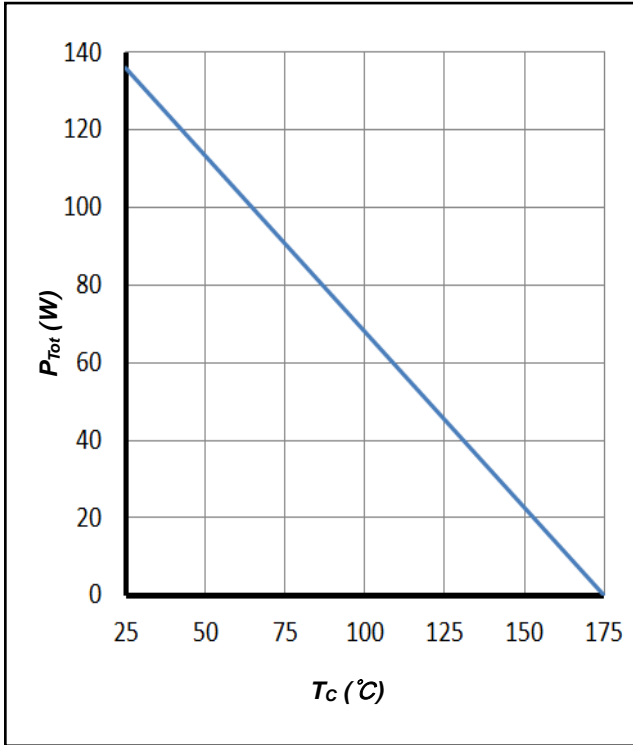


Figure 3. Power Derating

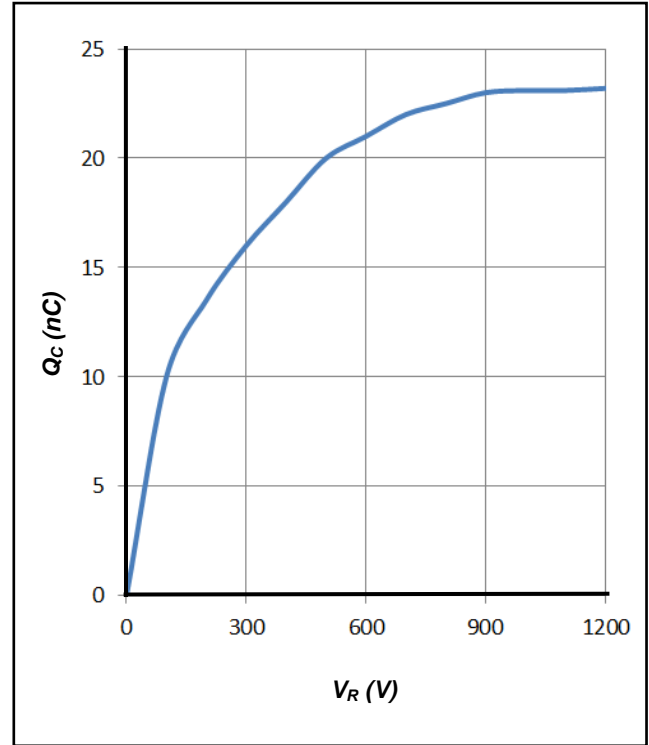


Figure 4. Total Capacitive Charge vs. Reverse Voltage

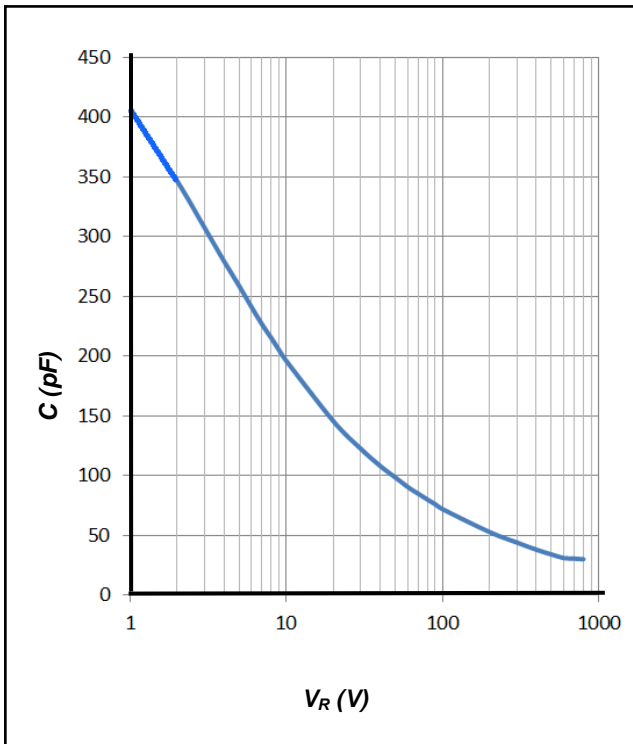


Figure 5. Total Capacitance vs. Reverse Voltage

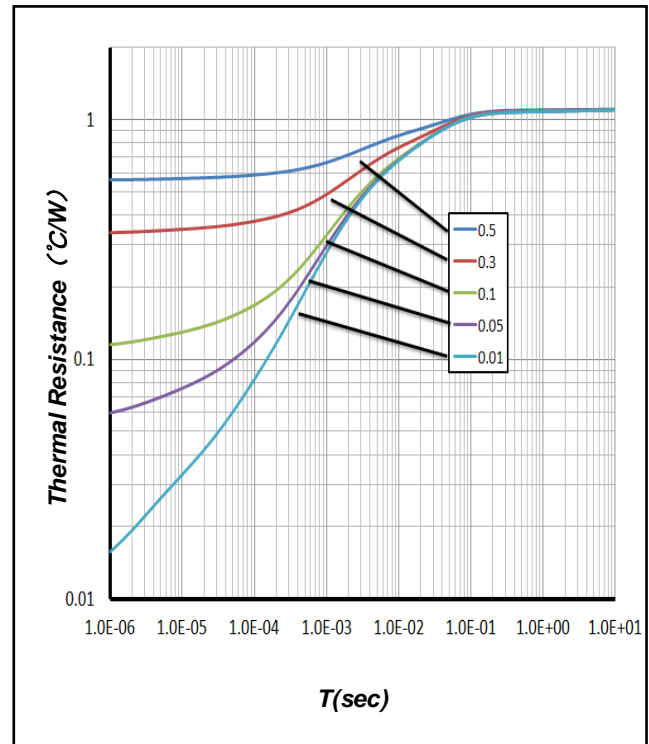
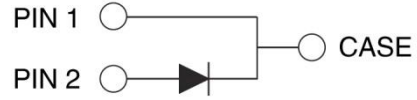
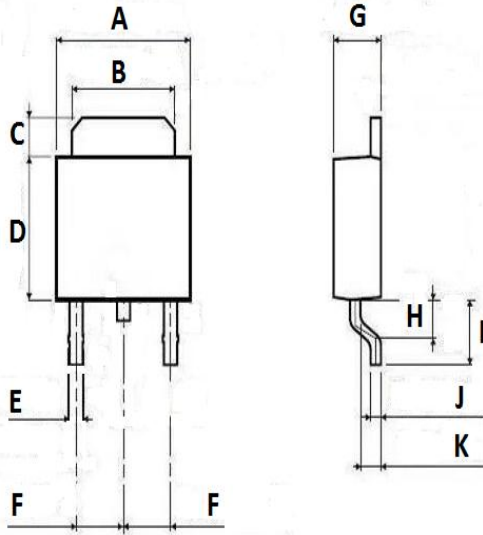


Figure 6. Transient Thermal Impedance

Package Dimensions

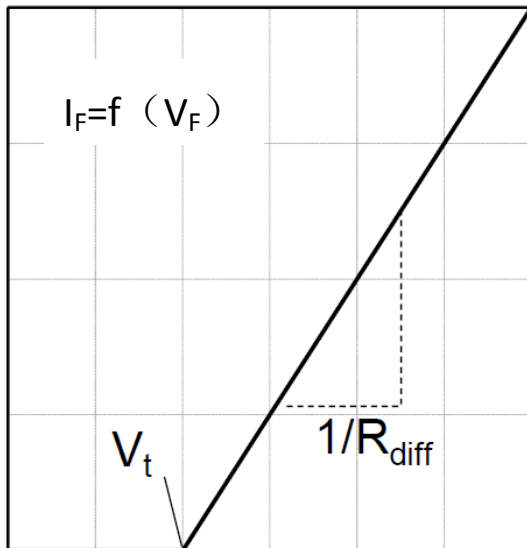
Package TO-252



Symbol	Min. (mm)	Typ. (mm)	Max. (mm)
A	6.3	6.5	6.7
B	5.2	5.3	5.4
C	1.15	1.25	1.35
D	5.7	5.9	6.1
E	0.65	0.7	0.75
F	2.1	2.3	2.5
G	2.2	2.3	2.4
H	1.45	1.5	1.55
I	2.9	3.0	3.1
J	0.45	0.5	0.55
K	0.9	1	1.1

Simplified Diode Model

Equivalent IV Curve for Model



Mathematical Equation

$$V_F = V_t + I_F \times R_{diff}$$

$$V_t = -0.0025 \times T_j + 0.99 \text{ [V]}$$

$$R_{diff} = 1.73 \times 10^{-6} \times T_j^2 + 3.64 \times 10^{-4} \times T_j + 0.066 \text{ [\Omega]}$$

Note:

T_j = Diode Junction Temperature In Degrees Celsius, valid from 25°C to 175°C

I_F = Forward Current

Less than 16A